



# **isc Silicon NPN Power Transistor**

#### **DESCRIPTION**

- High Power Dissipation
- · High Collector-Emitter Breakdown Voltage-
  - : V<sub>(BR)CEO</sub>= 350V(Min)
- · High Speed Switching
- · Low Collector Saturation Voltage
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

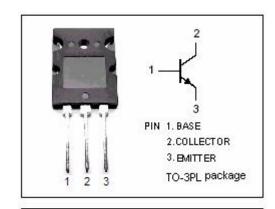
#### **APPLICATIONS**

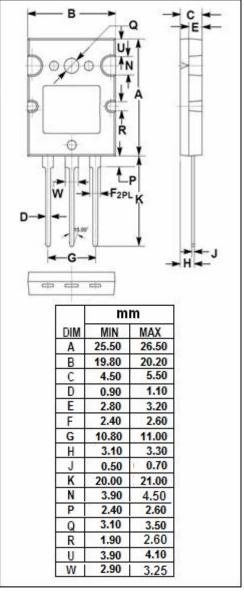


- High power amplifier applications.
- · High power switching applications.

## ABSOLUTE MAXIMUM RATINGS(Ta=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V <sub>CBO</sub>	Collector-Base Voltage	800	٧
VCEO	Collector-Emitter Voltage	350	V
V <sub>EBO</sub>	Emitter-Base Voltage	7	V
Ic	Collector Current-Continuous	25	Α
Ісм	Collector Current-Pulse	35	Α
I <sub>B</sub>	Base Current-Continuous	10	А
I <sub>BM</sub>	Base Current- Pulse us	15	Α
Pc	Collector Power Dissipation @ T <sub>C</sub> =25℃	200	W
TJ	Junction Temperature	150	$^{\circ}$
T <sub>stg</sub>	Storage Temperature Range	ge -55~150	





## isc Silicon NPN Power Transistor

2SD1313

#### **ELECTRICAL CHARACTERISTICS**

Tc=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT		
V <sub>(BR)CEO</sub>	Collector-Emitter Breakdown Voltage	I <sub>C</sub> = 10mA; I <sub>B</sub> = 0	350			V		
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	Ic= 15A; I <sub>B</sub> = 3A			1.0	V		
V <sub>BE(sat)</sub>	Base-Emitter Saturation Voltage	I <sub>C</sub> = 15A; I <sub>B</sub> = 3A			1.7	V		
I <sub>CBO</sub>	Collector Cutoff Current	V <sub>CB</sub> = 800V; I <sub>E</sub> = 0			1	mA		
I <sub>EBO</sub>	Emitter Cutoff Current	V <sub>EB</sub> = 7V; I <sub>C</sub> = 0			1	mA		
h <sub>FE-1</sub>	DC Current Gain	Ic= 1A; V <sub>CE</sub> = 5V	15					
h <sub>FE-2</sub>	DC Current Gain	I <sub>C</sub> = 25A; V <sub>CE</sub> = 5V	6					
Сов	Output Capacitance	I <sub>E</sub> =0; V <sub>CB</sub> = 50V; f <sub>test</sub> = 1MHz		170		pF		
f⊤	Current-Gain—Bandwidth Product	I <sub>C</sub> = 1A; V <sub>CE</sub> = 10V		6		MHz		
Switching Times								
t <sub>on</sub>	Turn-on Time	I <sub>C</sub> = 15A; I <sub>B1</sub> = I <sub>B2</sub> = 3A; R <sub>L</sub> = 13.3 Ω; V <sub>CC</sub> ≈ 200V P <sub>W</sub> =20 μ s; Duty Cycle≤1%		0.8		μS		
tstg	Storage Time			3.0		μS		
t <sub>f</sub>	Fall Time			0.5		μ <b>S</b>		

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